

**IN THE SPECIFICATION:**

Please amend the specification as follows:

After the TITLE please insert the following:

**--CROSS REFERENCE TO RELATED APPLICATION:**

The present application is a divisional of copending application Serial Number

09/313,027 filed on May 17, 1999.--

**IN THE CLAIMS**

Prior to examination please cancel claims 1-24 without prejudice.

Please add claims 25-50 as follows:

--25. A method for cleaning a semiconductor wafer having a copper layer exposed to a surface thereof after a chemical mechanical polishing, comprising the steps of:

a) treating said semiconductor wafer with a first washer selected from the group consisting of aqueous ammonia containing ammonia at 0.0001 – 0.5 weight percent and a catholyte between neutral and weak base for removing polishing particles from said semiconductor wafer without damage to said copper layer; and

b) treating said semiconductor wafer with a second washer containing at least one decontaminating agent selected from the group consisting of polycarboxylic acids each capable of producing a chelate compound together with copper, ammonium salts of said polycarboxylic acids and polyaminocarboxylic acids for removing metallic contaminants from said semiconductor wafer.